## Pt layer thickness dependence of voltage induced *interfacial* Dzyaloshinskii-Moriya interaction change in Fe|Pt|MgO junction

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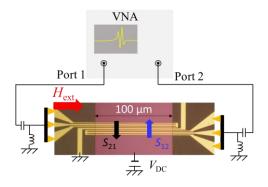
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*Interfacial* Dzyaloshinskii-Moriya interaction (*i*DMI) is an antisymmetric exchange interaction attributed to broken inversion symmetry in surfaces and/or interfaces together with spin-orbit interaction [1]. This *i*DMI modulates magnetism drastically and is voltage controllable [2]. Previously [3], we presented the enhancement of voltage-induced *i*DMI change by the factor of three by the insertion of Pt monolayer into the Fe|MgO interface. In present research, we studied thickness dependence of the Pt layers for voltage-induced *i*DMI change and the possible mechanisms of it.

The multilayers including Fe(20 nm)|Pt( $t_{Pt}$ =0.1-0.8 nm)|MgO(5 nm) were prepared on a V(001) underlayer. Figure 1 shows a schematic image of the spin-wave device and measurement circuit. Spin-wave spectra were measured by using vector network analyzer (VNA) through the two micro-sized antennas. External magnetic field was applied normal to the propagation direction in order to induce magnetostatic surface spin waves in Fe. By applying DC Voltage ( $V_{DC}$ ), voltage modulation of spin waves was observed. From the voltage modulation of spin-wave resonant frequency shift, we estimated the voltage controlled magnetic anisotropy (VCMA) and voltage induced *i*DMI change. Figure 2 shows Pt layer thickness dependence of (a) VCMA and (b) *i*DMI change. As you can see, largest enhancements of VCMA and voltage induced *i*DMI change were observed in 0.2-nm-thickness Pt. We discuss the possible mechanisms of these enhancement in terms of spin-orbit interaction and electric dipole.

This work was partially funded by ImPACT Program, JSPS KAKENHI (No. JP26103002) and Grant-in-Aid for JSPS Fellows.



n Pt 1 ML -40 fJ(Vm) -80 120 160 iDMI chang Julm<sup>-2</sup> at 5 V) 1.5 1.0 0.5 ł 0 0 0.2 0.4 0.6 0.8 Pt thickness (nm) Figure 2 Pt thickness dependence of(a) VCMA

Figure 1 Measurement set up and spin-wave device

and (b) voltage induced iDMI change at 5 V

[3] K. Nawaoka, et al., JSAP spring meeting 22a-W241-6 (2016)

<sup>[1]</sup> M. Bode, et al., Nature, 447, 190-193 (2007).

<sup>[2]</sup> K. Nawaoka, et al., APEX, 8, 063004(2015).